

N-Channel Trench Power MOSFET

General Description

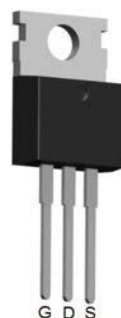
The MST7075 is N-channel MOS Field Effect Transistor designed for high current switching applications. Rugged EAS capability and ultra low $R_{DS(ON)}$ is suitable for PWM, load switching especially for E-Bike controller applications.

Features

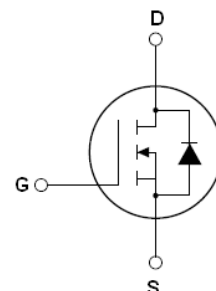
- $V_{DS}=70V$; $I_D=75A @ V_{GS}=10V$;
 $R_{DS(ON)} < 8.4m\Omega @ V_{GS}=10V$
- Special Designed for E-Bike Controller Application
- Ultra Low On-Resistance
- High UIS and UIS 100% Test

Application

- 48V E-Bike Controller Applications
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



To-220 Top View



Schematic Diagram

$$V_{DS} = 70 V$$

$$I_D = 75A$$

$$R_{DS(ON)} = 7m\Omega$$

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MST7075	MST7075	TO-220	-	-	-

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	70	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	±25	V
$I_{D(DC)}$	Drain Current (DC) at $T_c=25^\circ C$	75	A
$I_{D(DC)}$	Drain Current (DC) at $T_c=100^\circ C$	47.6	A
$I_{DM(pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	272	A
dv/dt	Peak Diode Recovery Voltage	30	V/ns
P_D	Maximum Power Dissipation($T_c=25^\circ C$)	85	W
	Derating Factor	0.57	W/°C
EAS	Single Pulse Avalanche Energy (Note 2)	360	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	°C

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature



2.EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=33\text{V}$, $V_G=10\text{V}$, $I_D=48.5\text{A}$

Table 2. Thermal Characteristic

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.77	$^{\circ}\text{C/W}$

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	70			V
I_{DSS}	Zero Gate Voltage Drain Current ($T_C=25^{\circ}\text{C}$)	$V_{DS}=68\text{V}$, $V_{GS}=0\text{V}$			1	μA
I_{DSS}	Zero Gate Voltage Drain Current ($T_C=125^{\circ}\text{C}$)	$V_{DS}=68\text{V}$, $V_{GS}=0\text{V}$			10	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 25\text{V}$, $V_{DS}=0\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2		4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=10\text{V}$, $I_D=40\text{A}$		7	8.4	m Ω
Dynamic Characteristics						
g_{FS}	Forward Transconductance	$V_{DS}=10\text{V}$, $I_D=40\text{A}$		28		S
C_{iss}	Input Capacitance	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$		2708		pF
C_{oss}	Output Capacitance			353		pF
C_{rss}	Reverse Transfer Capacitance			168		pF
Q_g	Total Gate Charge		$V_{DS}=50\text{V}$, $I_D=40\text{A}$, $V_{GS}=10\text{V}$		64	
Q_{gs}	Gate-Source Charge			13.4		nC
Q_{gd}	Gate-Drain Charge			26.2		nC
Switching Times						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30\text{V}$, $I_D=2\text{A}$, $R_L=15\Omega$ $V_{GS}=10\text{V}$, $R_G=2.5\Omega$		9		nS
t_r	Turn-on Rise Time			11		nS
$t_{d(off)}$	Turn-Off Delay Time			19		nS
t_f	Turn-Off Fall Time			23		nS
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)			75		A
I_{SDM}	Pulsed Source-Drain Current (Body Diode)			272		A
V_{SD}	Forward On Voltage ^(Note 1)	$T_J=25^{\circ}\text{C}$, $I_{SD}=40\text{A}$, $V_{GS}=0\text{V}$		0.79	0.95	V
t_{rr}	Reverse Recovery Time ^(Note 1)	$T_J=25^{\circ}\text{C}$, $I_F=75\text{A}$ $di/dt=100\text{A}/\mu\text{s}$		34		nS
Q_{rr}	Reverse Recovery Charge ^(Note 1)			69		nC

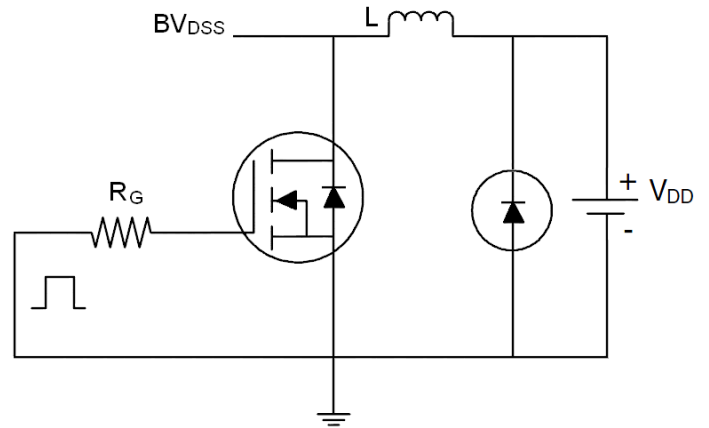
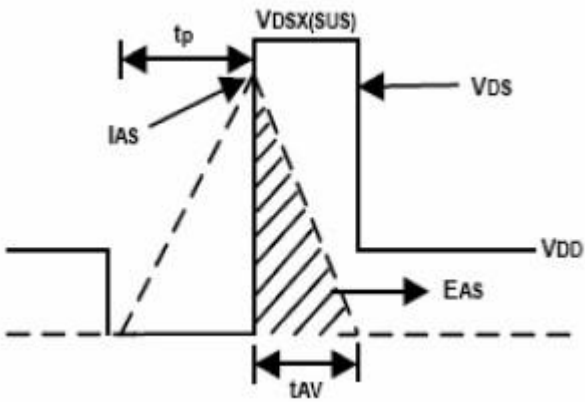


t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible(turn-on is dominated by L_s+L_D)
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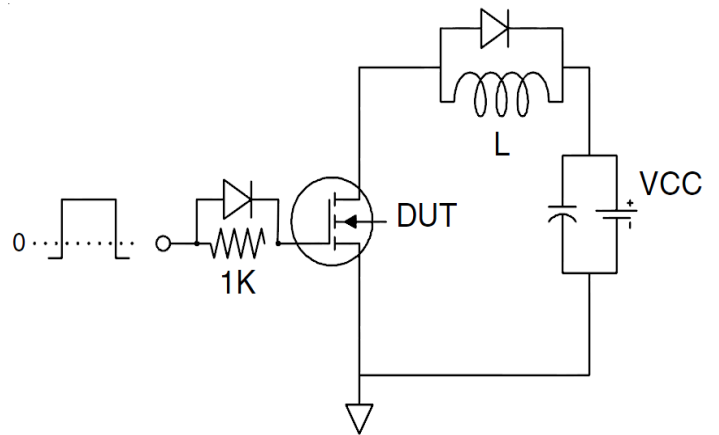
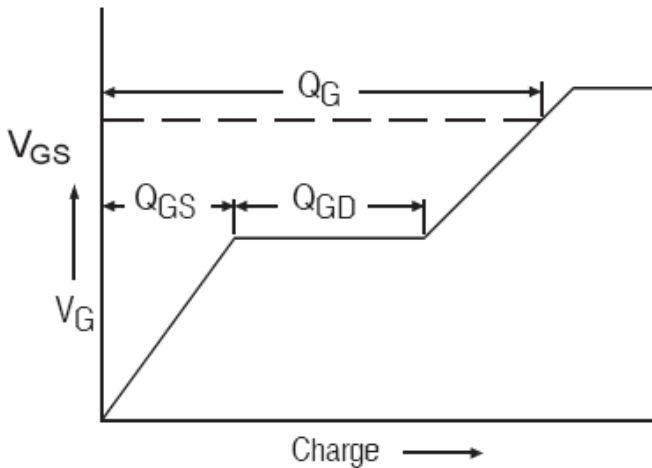
Notes 1.Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1.5\%$, $R_G=25\Omega$, Starting $T_J=25^\circ C$

Test Circuit

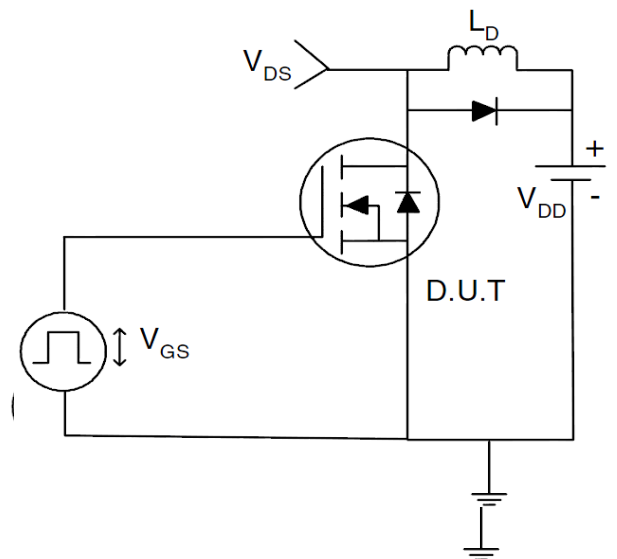
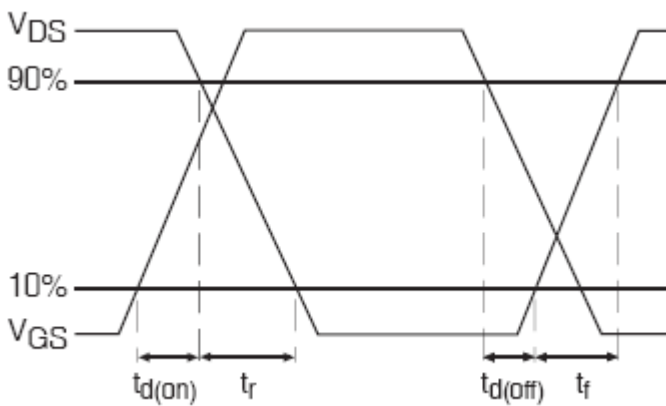
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Safe Operating Area

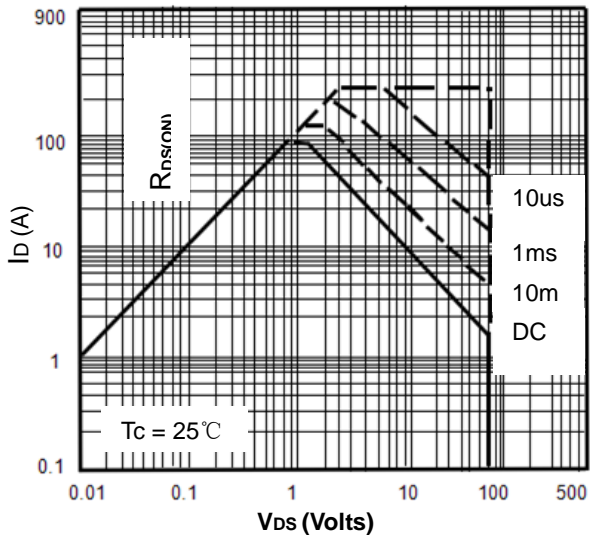


Figure2. Source-Drain Diode Forward Voltage

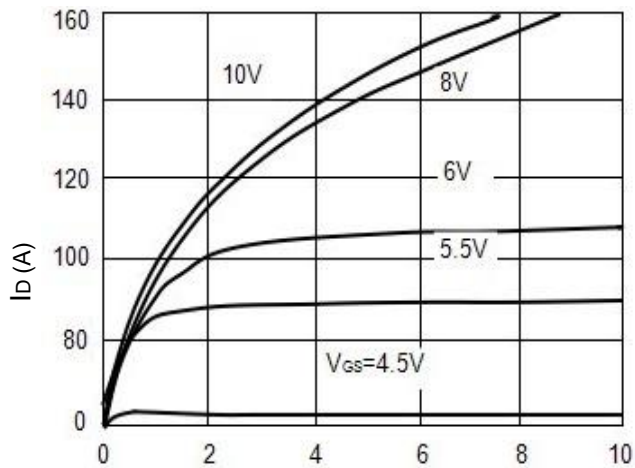
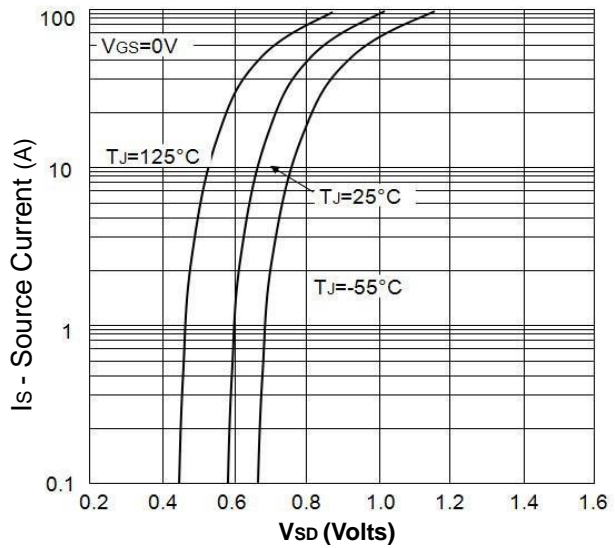


Figure3. Output Characteristics

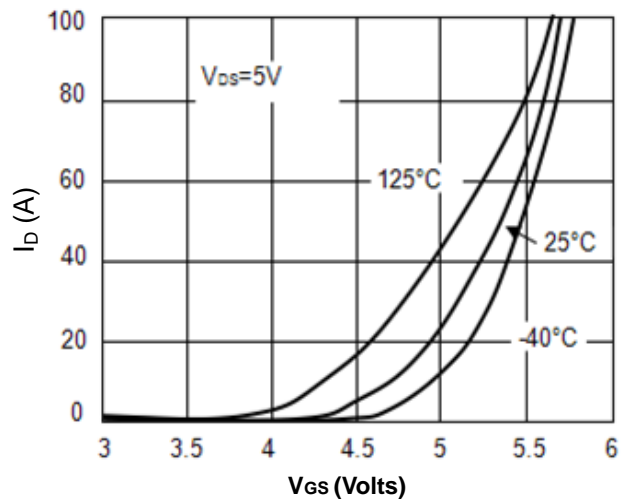


Figure5. Static Drain-Source On Resistance

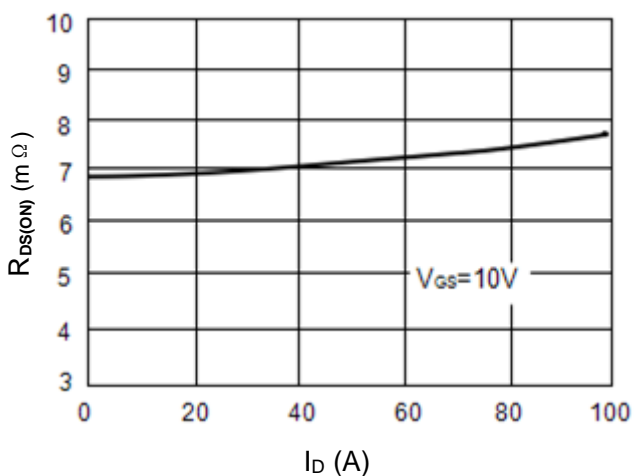


Figure6. RDS(ON) vs Junction Temperature

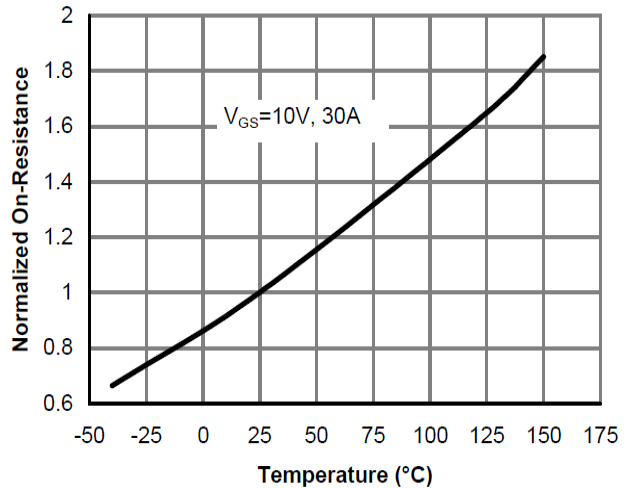


Figure7. BV_{DSS} vs Junction Temperature

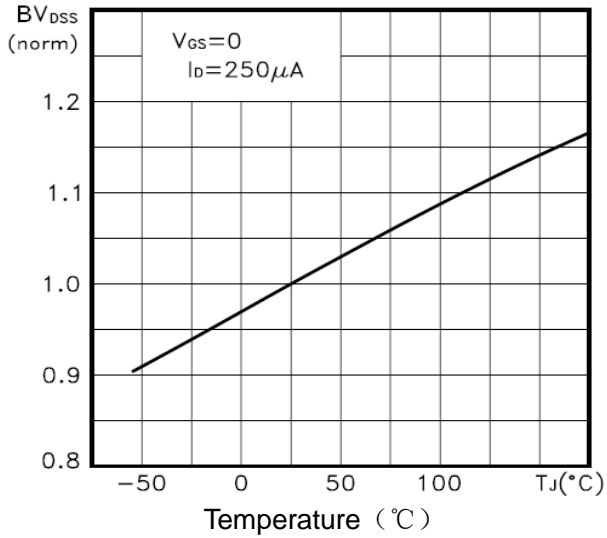


Figure8. $V_{GS(th)}$ vs Junction Temperature

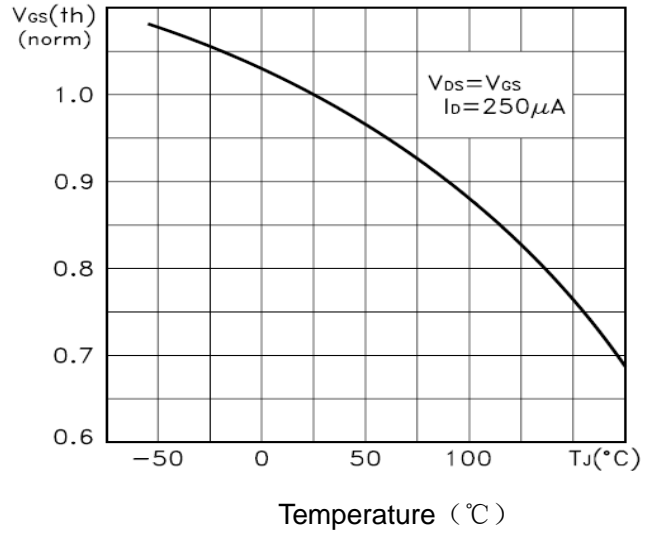


Figure9. Gate Charge Waveforms

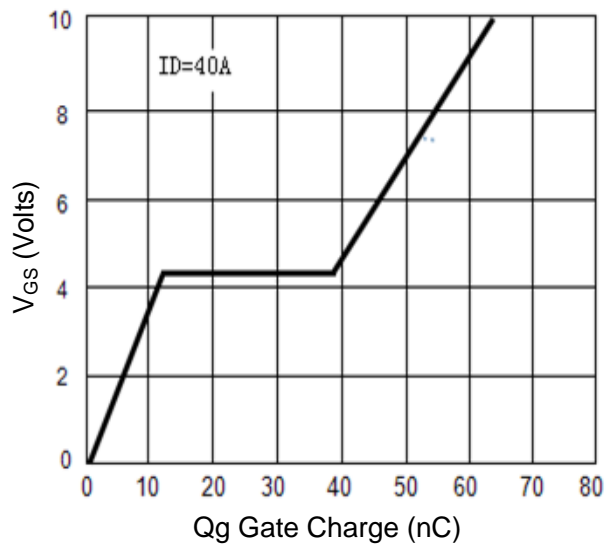


Figure10. Capacitance

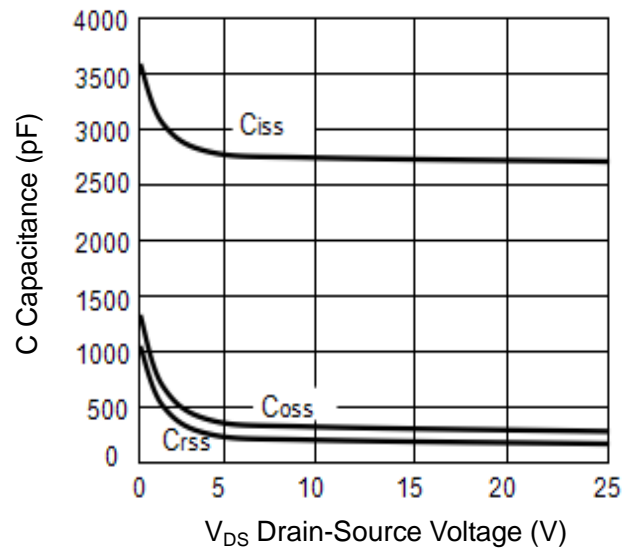
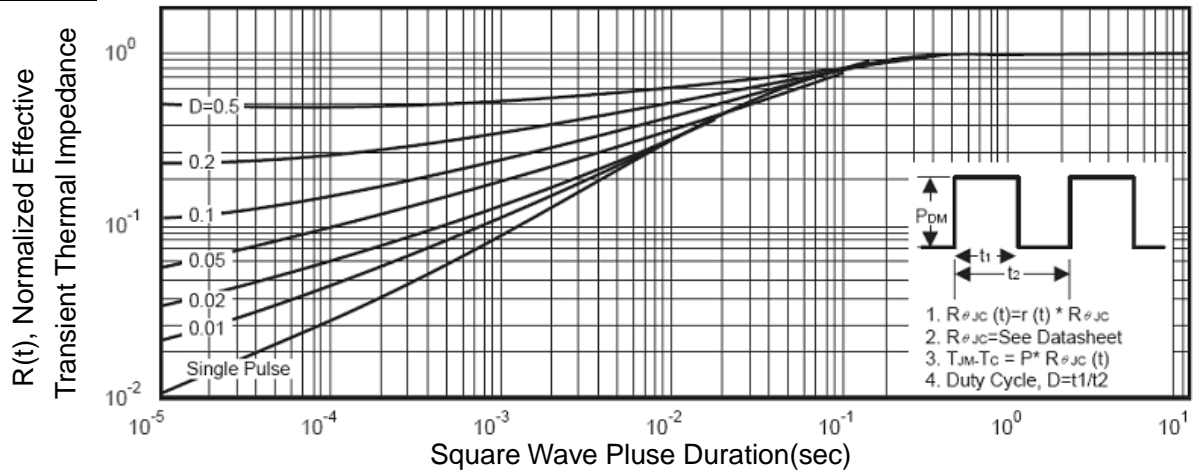
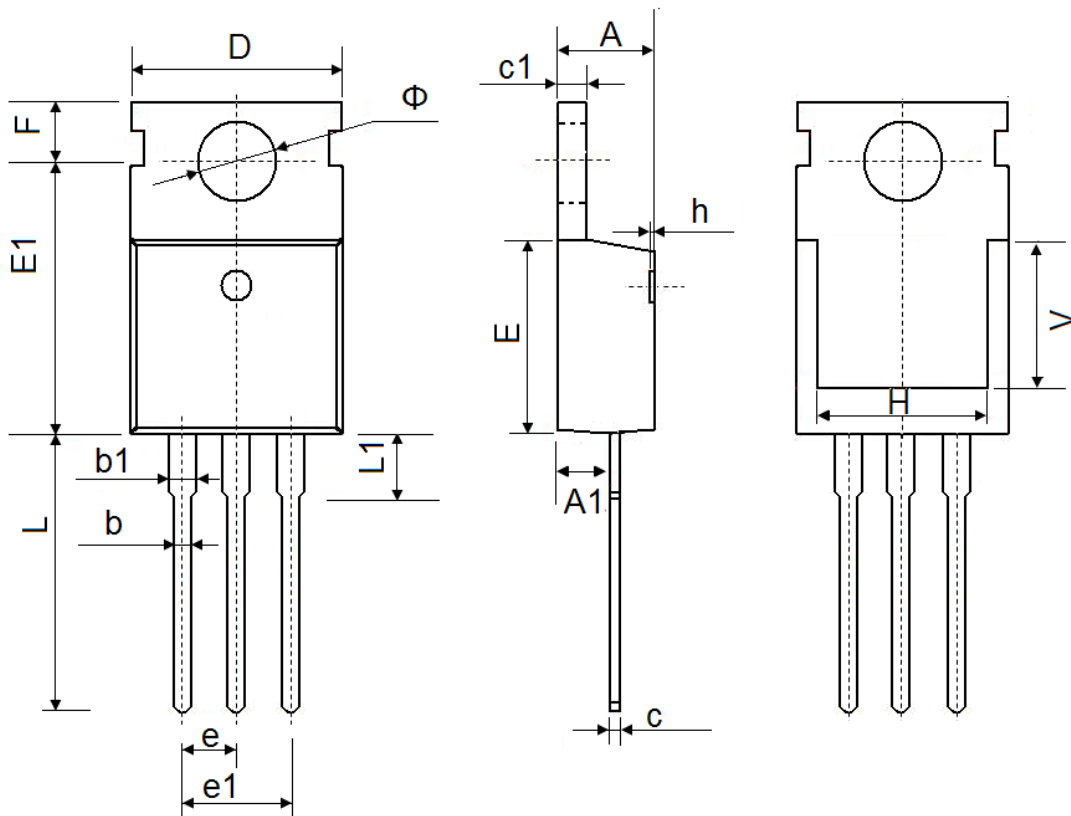


Figure11. Normalized Maximum Transient Thermal Impedance



TO-220 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055



D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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